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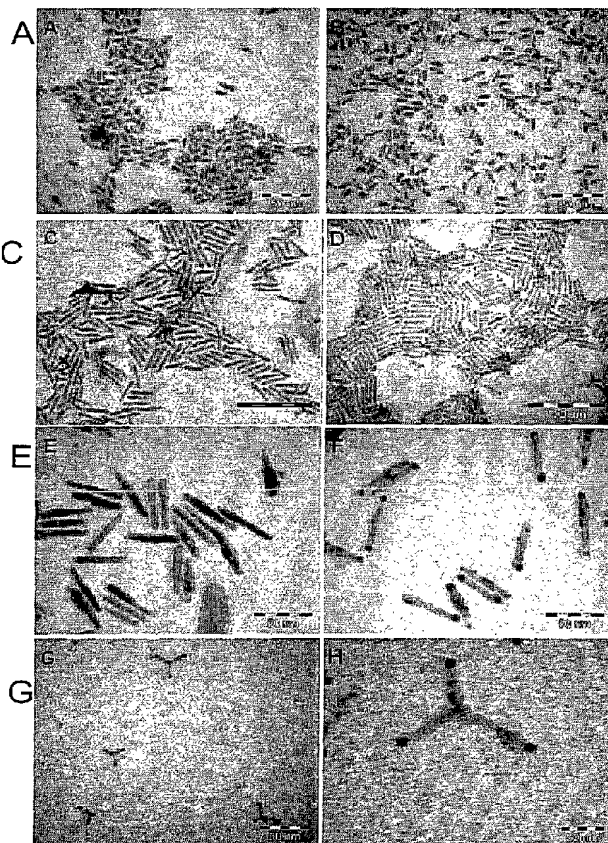
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(54) Title: NOVEL NANOSTRUCTURES AND METHOD FOR SELECTIVE PREPARATION



(57) Abstract: The present invention provides novel  
nanostructure composed of at least one elongated  
structure element, an elongated structure element  
of said nanostructure bearing a different zone  
made of metal, metal alloy, conductive polymer or  
semiconductor and selectively grown onto at least  
one of the end portions of the elongated structure  
element. The present invention further provides a  
selective method for forming in a liquid medium, such  
nanostructures.

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